

## AMENDMENT TRANSMITTAL LETTER

Docket No.  
M4065.0210/P210Application No.  
09/588,008Filing Date  
June 6, 2000Examiner  
Hoa B. TrinhArt Unit  
2814

Applicant(s): Yang, et al.

Invention: IMPROVED MEMORY CELL CAPACITOR STRUCTURE AND METHOD OF FORMATION

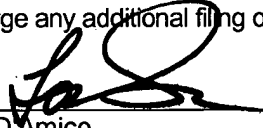
## TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

## CLAIMS AS AMENDED

|  | Claims<br>Remaining<br>After<br>Amendment | Highest<br>Number<br>Previously<br>Paid | Number<br>Extra Claims<br>Present | Rate    |        |
|--|---|---|-----------------------------------|---------|--------|
| Total Claims   | 33  | - 20 =                                  | 13                                | x 18.00 | 234.00 |
| Independent<br>Claims  | 3   | - 3 =                                   | 0                                 | x       | 0.00   |
| Multiple Dependent Claims (check if applicable) <input type="checkbox"/> |   |   |                                   |         |        |
| Other fee (please specify):  |   |   |                                   |         |        |
| TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:                                 |   |   |                                   |         |        |

☒ Large Entity☐ Small Entity☐ No additional fee is required for this amendment.☐ Please charge Deposit Account No. \_\_\_\_\_ in the amount of \$ \_\_\_\_\_.  
A duplicate copy of this sheet is enclosed.☐ A check in the amount of \$ \_\_\_\_\_ to cover the filing fee is enclosed.☐ Payment by credit card. Form PTO-2038 is attached.☒ The Commissioner is hereby authorized to charge and credit Deposit Account No. 04-1073  
as described below. A duplicate copy of this sheet is enclosed.☒ Credit any overpayment.☒ Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.  
Thomas J. D'Amico  
Attorney Reg. No.: 28,371

Dated: September 4, 2002

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Docket No.: M4065.0210/P210  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:  
Yang et al.

Application No.: 09/588,008

Group Art Unit: 2814

Filed: June 6, 2000

Examiner: Vikki H. Trinh

For: IMPROVED MEMORY CELL CAPACITOR  
STRUCTURE AND METHOD OF  
FORMATION

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9/13/02  
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AMENDMENT UNDER 37 CFR §1.116

ATTN: BOX AF  
Commissioner for Patents  
Washington, DC 20231

Dear Sir:

This paper is in response to the Office Action dated June 4, 2002 finally rejecting claims 1-31, 97, and 98, please amend the above-captioned U.S. Patent application as follows:

In the Claims:

Please replace claims 1, 97, and 98 with amended claims 1, 97, and 98 below.

1. (amended) A capacitor for a semiconductor device, said capacitor comprising:

a bottom conducting layer;

a dielectric layer formed over said bottom conducting layer; and

an annealed oxygen permeable top conducting layer formed over said dielectric